HVC133

Silicon Epitaxial Planar Pin Diode for High Frequency Switching

HITACHI

ADE-208-423A(Z)
Rev 1
September 1996

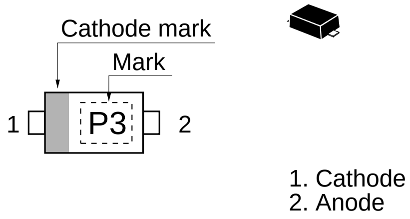
Features

- Low capacitance.(C1=1.0pF max)
- Low forward resistance. (rf=0.7Ω max)
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVC133	P3	UFP

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	30	V
Power dissipation	Pd	150	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55Å`+125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	VR	30	Å\	Å\	V	IR = 1µA
Reverse current	IR	Å\	Å\	100	nA	VR = 25V
Forward voltage	VF	Å\	Å\	0.85	V	IF = 2 mA
Capacitance	C1	Å\	Å\	1.0	pF	VR = 1V, f = 1 MHz
	C6	Å\	Å\	0.9		VR = 6V, f = 1 MHz
Forward resistance	rf	Å\	0.55	0.7	Ω	IF = 2mA, f = 100 MHz

Main Characteristic

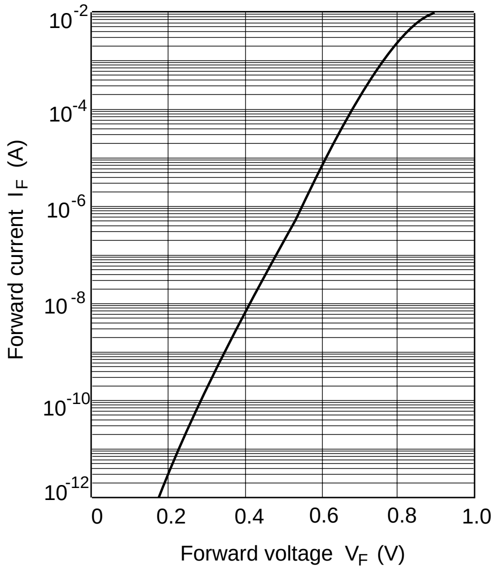

Fig.1 Forward current Vs. Forward voltage

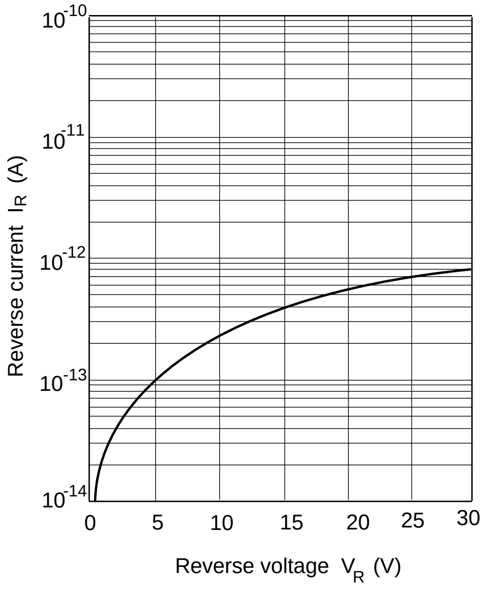

Fig.2 Reverse current Vs. Reverse voltage

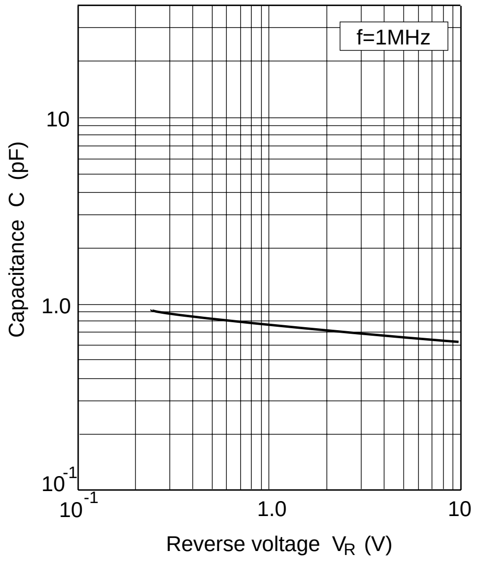

Fig.3 Capacitance Vs. Reverse voltage

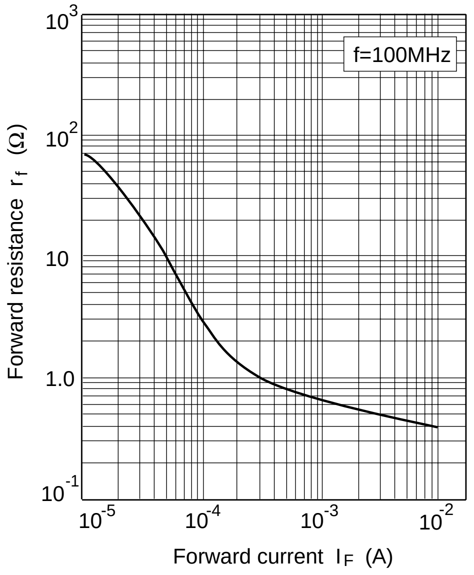

Fig.4 Forward resistance Vs. Forward current

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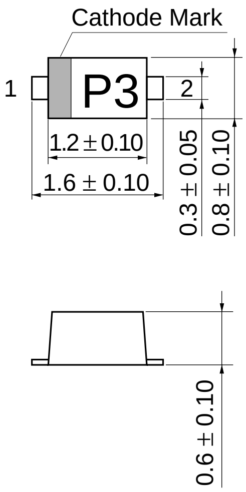
Package Dimensions

Unit : mm



1. Cathode
2. Anode

Hitachi Code	UFP
JEDECCode	—
EIAJCode	SC-79
Weight(g)	0.0016